



Attorney Docket No.: 09792909.5171
Customer No.: 26263

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Toshiharu YANAGIDA

Application No.: 09/915,160

Confirmation No.: 7228

Filed: July 25, 2001

For: SEMICONDUCTOR APPARATUS AND PROCESS OF PRODUCTION THEREOF

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner Of Patents and Trademarks
Washington, D.C. 20231

Sir:

In response to the Non-Final Office Action dated November 6, 2002, Paper No. 6, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please replace page 30, the fourth full paragraph, continuing to page 31, with the following new paragraph:

B1
In Fig. 6, the plasma treatment device 300 is a so-called triode type RF plasma treatment device comprised of a sealed plasma treatment chamber 301, an anode plate 302 provided at the top inside the plasma treatment chamber 301, a stage 303 serving as a cathode plate provided at the bottom, a lattice electrode 304 provided between the anode plate 302 and the stage 303, a coupling capacitor 305 through which a plasma generation power source 306 is connected to the cathode plate 302, and a coupling capacitor 307 through which a substrate bias power source 308 is connected to the stage 303.

IN THE CLAIMS:

Please cancel Claims 3/4 without prejudice or disclaimer.

#8/B
Amend
Unpublished
3/12/02
RECEIVED
MAR 11 2003
TECHNOLOGY CENTER 2800